Product Specification Sheet

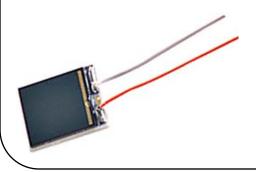


FDS1010

Photodiodes

Description

The Thorlabs FDS1010 photodiode is ideal for measuring both pulsed and CW fiber light sources, by converting the optical power to an electrical current. The detector is an un-housed ceramic wafer with anode and cathode lead wires. The photodiode anode produces a current, which is a function of the incident light power and the wavelength. The responsivity $\Re(\lambda)$, can be read from the responsivity



graph to estimate the amount of photocurrent to expect. This can be converted to a voltage by placing a load resistor (R_L) from the photodiode anode to the circuit ground. The output voltage is derived as:

$$V_o = P \times \Re(\lambda) \times R_L$$

The bandwidth, f_{BW} , and the rise time response, t_R , are determined from the diode capacitance, C_J , and the load resistance, R_L , as shown below. Placing a bias voltage from the photo diode cathode to the circuit ground can lower the photo diode capacitance.

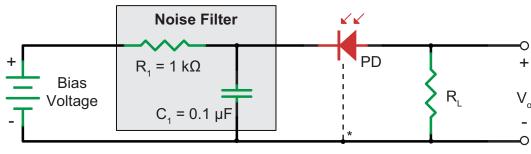
$$f_{BW} = rac{1}{2\pi(R_L)C_j}, t_R = rac{0.35}{f_{BW}}$$

Specifications

Specification	Value	Specification	Value
Wavelength Range	400 - 1100 nm	Sensor Material	Si PIN
Active Area	9.7 mm x 9.7 mm (94 mm ²)	Max Ratings	
Rise/Fall Time (R_L =50 Ω , 5 V)	45 ns	Damage Threshold, CW	n/a
Bandwidth (R_L =50 Ω , -3 dB, 5 V)	8 MHz	Damage Threshold, 10 ns Pulse	n/a
NEP (900 nm)	$5.5 \text{ x } 10^{-14} \text{ W/Hz}^{\frac{1}{2}}$	Max Bias (Reverse) Voltage	25 V
Dark Current, Max (5 V)	600 nA	Operating Temperature	-10 to 60 °C
Capacitance, Typical (5 V)	375 pF	Storage Temperature	-20 to 70 °C
Package	Ceramic Wafer	Reverse Current	10 mA
		Forward Current	10 mA

Recommended Circuit Diagram

Application of a reverse bias can greatly improve the response speed and linearity of the device. This is due to increase in the depletion region width and, consequently, decrease in junction capacitance. However, the dark current and noise will increase.



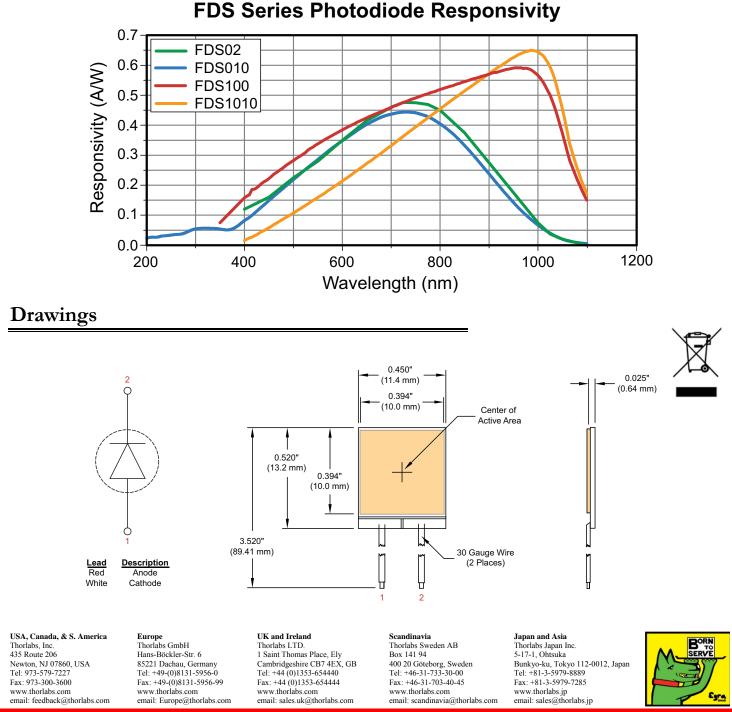
* Case ground for PD with a third lead.

Graphs

The responsivity of a photodiode is a measure of its sensitivity to light, and it is defined as the ratio of the photocurrent I_P to the incident light power P at a given wavelength:

$$R_{\lambda} = \frac{I_P}{P}$$

In other words, it is a measure of the effectiveness of the conversion of light power into electrical current. Responsivity varies from lot to lot and with the wavelength of the incident light, applied reverse bias, and temperature. It increases slightly with applied reverse bias due to improved charge collection efficiency in the photodiode. The change in temperature increases or decreases the width of the band gap and varies inversely with the temperature.



2739-S01 Rev D – Jan 09, 2010 Specifications subject to change without notice.